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NST45011MW6T1G, NSVT45011MW6T3G

Dual Matched General Purpose Transistor

NPN Matched Pair

These transistors are housed in an ultra-small SOT-363 package ideally suited for portable products. They are assembled to create a pair of devices highly matched in all parameters, eliminating the need for costly trimming. Applications are Current Mirrors; Differential, Sense and Balanced Amplifiers; Mixers; Detectors and Limiters.

Features

- Current Gain Matching to 10%
- Base-Emitter Voltage Matched to 2 mV
- Drop-In Replacement for Standard Device
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|-----------|-------|------------------|
| Collector - Emitter Voltage | V_{CEO} | 45 | V |
| Collector - Base Voltage | V_{CBO} | 50 | V |
| Emitter - Base Voltage | V_{EBO} | 6.0 | V |
| Collector Current - Continuous | I_C | 100 | mA _{dc} |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|---------------------------|
| Total Device Dissipation Per Device | P_D | 380 | mW |
| FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C | | 250 | |
| | | 3.0 | mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 328 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

1. FR-5 = 1.0 x 0.75 x 0.062 in

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

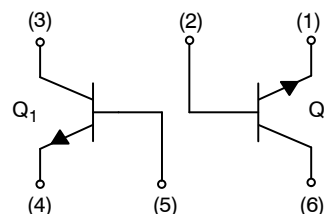


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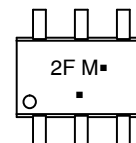
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SOT-363
CASE 419B
STYLE 1



MARKING DIAGRAMS



2F = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|-----------------|----------------------|-------------------------|
| NST45011MW6T1G | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| NSVT45011MW6T3G | SOT-363 (Pb-Free) | 10,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST45011MW6T1G, NSVT45011MW6T3G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---|-------------------|-----------------|-------------------|----------|
| OFF CHARACTERISTICS | | | | | |
| Collector – Emitter Breakdown Voltage, (I _C = 10 mA) | V _{(BR)CEO} | 45 | – | – | V |
| Collector – Emitter Breakdown Voltage, (I _C = 10 μA, V _{EB} = 0) | V _{(BR)CES} | 50 | – | – | V |
| Collector – Base Breakdown Voltage, (I _C = 10 μA) | V _{(BR)CBO} | 50 | – | – | V |
| Emitter – Base Breakdown Voltage, (I _E = 1.0 μA) | V _{(BR)EBO} | 6.0 | – | – | V |
| Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C) | I _{CBO} | – | – | 15 5.0 | nA μA |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V) (Note 2) | h _{FE} h _{FE(1)}/h_{FE(2)}}} | 150 200 0.9 | – 300 1.0 | – 500 1.1 | – |
| Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) | V _{CE(sat)} | – – | – – | 250 600 | mV |
| Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) | V _{BE(sat)} | 700 850 | 750 890 | 800 950 | mV |
| Base – Emitter On Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V) (Note 3) | V _{BE(on)} V _{BE(1)} – V_{BE(2)}}} | 580 – – | 660 – 1.0 | 700 770 2.0 | mV |
| SMALL-SIGNAL CHARACTERISTICS | | | | | |
| Current – Gain – Bandwidth Product, (I _C = 10 mA, V _{CE} = 5 Vdc, f = 100 MHz) | f _T | 100 | – | – | MHz |
| Output Capacitance, (V _{CB} = 10 V, f = 1.0 MHz) | C _{ob} | – | – | 4.5 | pF |
| Noise Figure, (I _C = 0.2 mA, V _{CE} = 5 Vdc, R _S = 2 kΩ, f = 1 kHz, BW = 200Hz) | NF | – | – | 10 | dB |
| Noise Figure, (I _C = 0.1 mA, V _{CE} = 10 Vdc, R _S = 1 kΩ, f = 1 kHz, BW = 200Hz) | NF | – | 1.0 | – | dB |

2. h<sub>FE(1)}/h_{FE(2)}} is the ratio of one transistor compared to the other transistor within the same package. The smaller h_{FE} is used as numerator.
 3. V_{BE(1)} – V_{BE(2)}} is the absolute difference of one transistor compared to the other transistor within the same package.}</sub>

TYPICAL CHARACTERISTICS

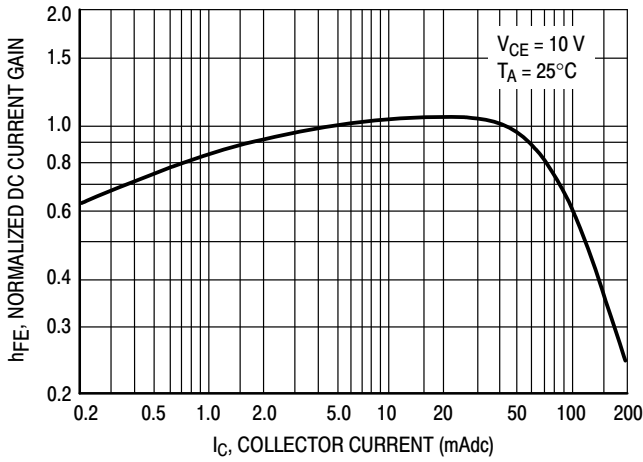


Figure 1. Normalized DC Current Gain

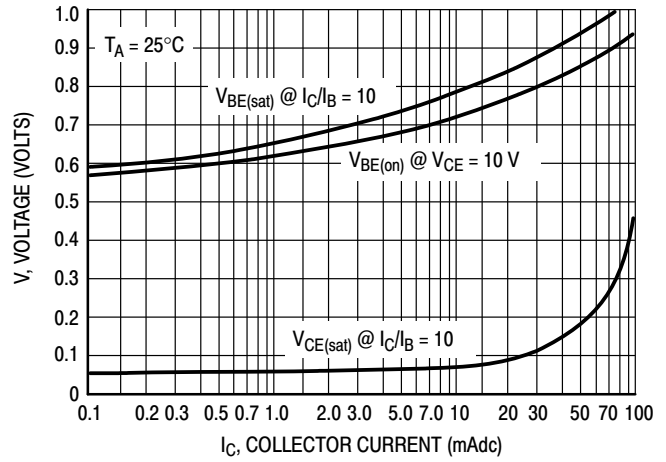


Figure 2. "Saturation" and "On" Voltages

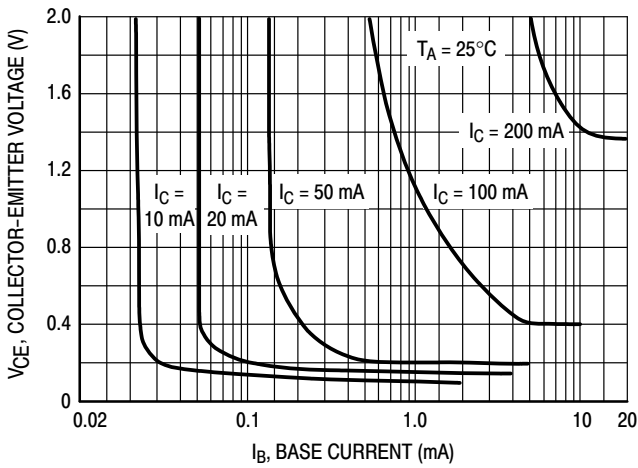


Figure 3. Collector Saturation Region

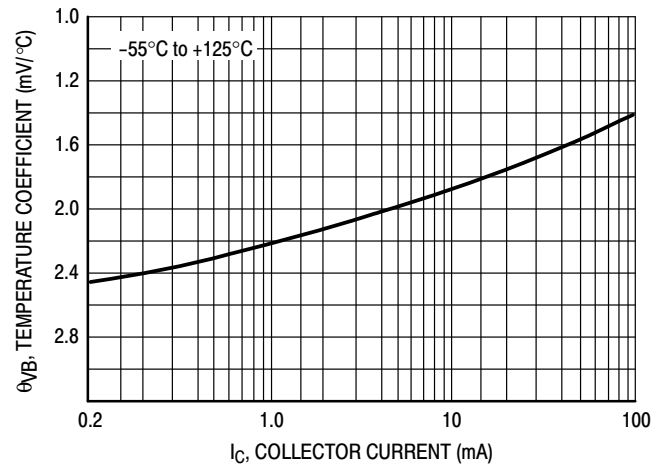


Figure 4. Base-Emitter Temperature Coefficient

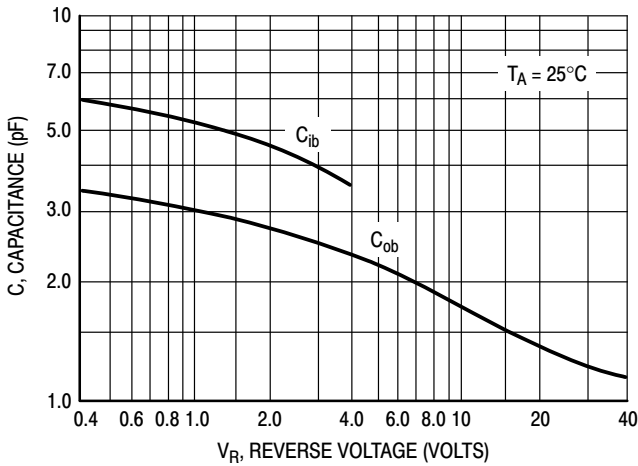


Figure 5. Capacitances

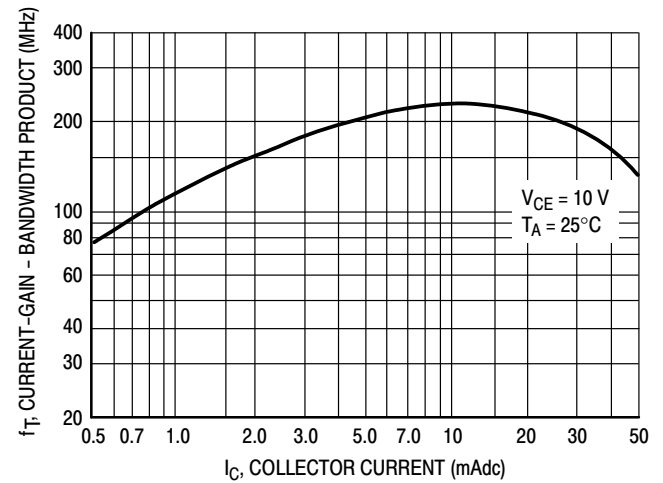


Figure 6. Current-Gain - Bandwidth Product

NST45011MW6T1G, NSVT45011MW6T3G

TYPICAL CHARACTERISTICS

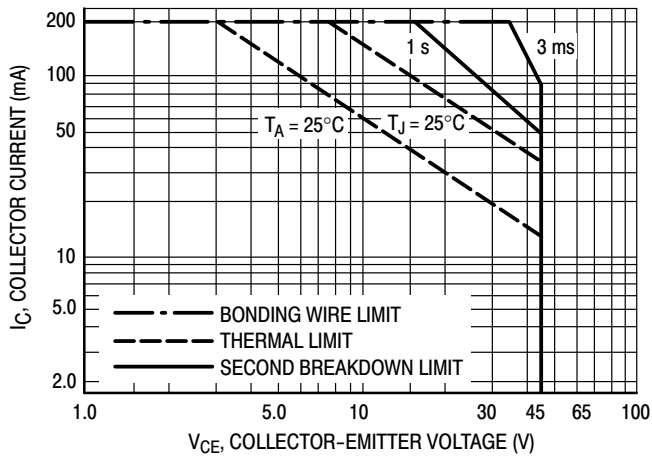


Figure 7. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 7 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

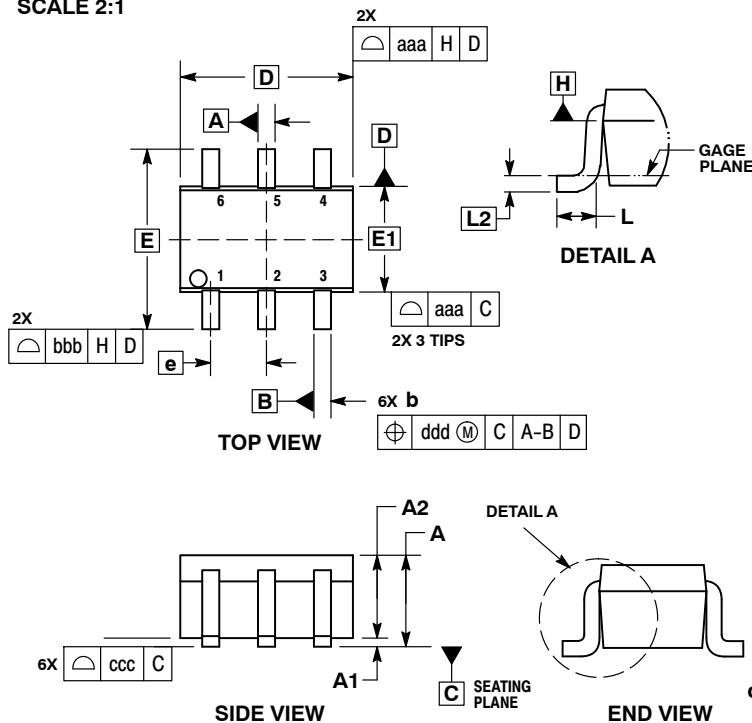
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SCALE 2:1

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

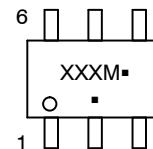
DATE 11 DEC 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | --- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC | | | 0.006 BSC | | |
| aaa | 0.15 | | | 0.006 | | |
| bbb | 0.30 | | | 0.012 | | |
| ccc | 0.10 | | | 0.004 | | |
| ddd | 0.10 | | | 0.004 | | |

GENERIC MARKING DIAGRAM*



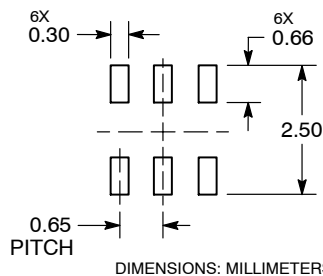
- XXX = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 419B-02
ISSUE Y

DATE 11 DEC 2012

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|---|---|--|--|--|--|
| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC | STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1 | STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1 | STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1 | STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1 |
| STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF | STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR | STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1 | STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c) | STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C | STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE |
| STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1 | STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1 | STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2 | STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN | STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE | STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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